L Number	Hits	Search Text	DB	Time stamp
1	0	(flash near2 anneal$3) near10 ((back or bottom) near5 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 20:54
2	0	(flash near2 anneal$3) near10 (imping$3 near5 (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 21:31
3	0	anneal$3 near10 (imping$3 near5 (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 21:32
4	0	anneal$3 same (imping$3 near5 (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 21:32
5	0	anneal$3 same (imping$3 or though) near5 (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 21:33
6	10	anneal$3 same ((imping$3 or through) near5 (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 21:35
7	8	(flash near2 anneal$3 same ((imping$3 or through) near5 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 21:35
-	6192	((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:34
-	17530	(soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:28
-	0	(((xe adj arc) near2 lamp) same anneal$3) near10 ((support or second silicon or quartz or semiconductor)near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:48
-	0	(((xe adj arc) near2 lamp) same anneal$3) same ((support or second silicon or quartz or semiconductor)near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:48
-	0	(((xe adj arc) near2 lamp) same anneal$3) same ((support or second or silicon or quartz or semiconductor)near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:49
-	0	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and ((((xe adj arc) near2 lamp) same anneal$3) and ((support or second or silicon or quartz or semiconductor)near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:49

-	26	(((xe adj arc) near2 lamp) same anneal$3) and ((support or second or silicon or quartz or semiconductor)near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:50
-	5	(((xe adj arc) near2 lamp) same (anneal$3 or heat$3)) near10 (substrate or (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:52
-	54	(((xe adj arc) near2 lamp) same (anneal$3 or heat$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:53
-	0	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and ((((xe adj arc) near2 lamp) same (anneal$3 or heat$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:53
-	206	(((xe adj arc) near2 lamp) and (anneal$3 or heat$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:03
-	0	(((((xe adj arc) near2 lamp) and (anneal$3 or heat$3))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (((438/149) or (438/311) or (438/458) or (438/473) or (438/474) or (438/475) or (438/477) or (438/479) or (438/480) or (438/495) or (438/496) or (438/499) or (438/406) or (438/508) or (438/509) or (438/514) or (438/787) or (438/788)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:53
-	34	(((((xe adj arc) near2 lamp) and (anneal$3 or heat$3))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 17:53
-	10693	wafer near2 bond$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:19
-	2450	((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:02
-	0	(((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond$3)) and ((((xe adj arc) near2 lamp) and (anneal$3 or heat$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:02
-	3933068	anneal$3 or heat$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:55
-	1808	(anneal$3 or heat$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:05

-	281	((xe adj arc) near2 lamp)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:03
-	0	((anneal$3 or heat$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond$3))) and (((xe adj arc) near2 lamp))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:04
-	40	((anneal$3 or heat$3) and (((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer)) and (wafer near2 bond$3))) and (lamp near5 intensit$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:29
-	15436	wafer near5 bond$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:20
-	8537	(wafer near5 bond$3) and (anneal$3 or heat$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:20
-	1232	implant$ near5 (hydrogen near ion$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:27
-	179	(wafer near5 bond$3) same (implant$ near5 (hydrogen near ion$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:57
-	162	((wafer near5 bond$3) same (implant$ near5 (hydrogen near ion$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:28
-	158	(((wafer near5 bond$3) same (implant$ near5 (hydrogen near ion$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal$3 or heat$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:28
-	2	((((wafer near5 bond$3) same (implant$ near5 (hydrogen near ion$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal$3 or heat$3)) and (lamp near5 intensit$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:38
-	37	(((((wafer near5 bond$3) same (implant$ near5 (hydrogen near ion$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (anneal$3 or heat$3)) and lamp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:31
-	366	(wafer near5 bond$3) and (implant$ near5 (hydrogen near ion$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:58

-	310	((wafer near5 bond$3) and (implant$ near5 (hydrogen near ion$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:58
-	0	(((wafer near5 bond$3) and (implant$ near5 (hydrogen near ion$1))) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (((anneal$3 or heat$3) same lamp) near5 (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:59
-	0	((wafer near5 bond$3) and (implant$ near5 (hydrogen near ion$1))) and (((anneal$3 or heat$3) same lamp) near5 (support near2 substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:59
-	0	(((anneal$3 or heat$3) same lamp) near5 (support near2 substrate)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 18:59
-	43	((anneal$3 or heat$3) same lamp) near5 (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:01
-	2013	(anneal$3 or heat$3) near3 (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:02
-	71	((anneal$3 or heat$3) near3 (support near2 substrate)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:02
-	16	(((anneal$3 or heat$3) near3 (support near2 substrate)) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))) and (implant$ near5 (hydrogen near ion$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:03
-	1	"5543636".PN.	USPAT	2004/08/20 19:22
-	4	("5854123" | "5882987" | "5953622" | "6010579").PN.	USPAT	2004/08/20 19:23
-	6	("5374564" | "5882987" | "6146979" | "6251754" | "6294814" | "6323108").PN.	USPAT	2004/08/20 19:24
-	1	("6376806").PN.	USPAT	2004/08/20 19:35
-	15	("4356384" | "4436985" | "4707217" | "4755654" | "5073698" | "5577157" | "5722761" | "5756369" | "5811327" | "5840118" | "5892332" | "5893952" | "5937282" | "6080965" | "6144171").PN.	USPAT	2004/08/20 19:36
-	335	flash near2 anneal$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:52
-	0	(flash near2 anneal$3) near5 (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:40
-	1	(flash near2 anneal$3) near10 (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:40

-	1	(flash near2 anneal$3) same (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:40
-	7	(flash near2 anneal$3) and (support near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:44
-	0	(flash near2 anneal$3) near5 (separt$5 same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:45
-	0	(flash near2 anneal$3) near5 separt$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:45
-	0	(flash near2 anneal$3) near10 separt$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:46
-	2	(flash near2 anneal$3) near10 (through near5 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:47
-	1	(flash near2 anneal$3) near10 (through near2 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:48
-	1	(flash near2 anneal$3) near10 (through same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:48
-	27	(flash near2 anneal$3) near10 (substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:50
-	1	(flash near2 anneal$3) same (hydrogen near2 ion$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:29
-	18	flash near2 anneal$3 and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:55
-	42016	flash near2 anneal$3 or ((xe adj arc) near2 lamp) or xenon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 18:41
-	20	(flash near2 anneal$3 or ((xe adj arc) near2 lamp) or xenon) same ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)) near3 (substrate or wafer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 19:56
-	41728	((xe adj arc) near2 lamp) or xenon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:30

-	40914	(soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:28
-	869	(((xe adj arc) near2 lamp) or xenon) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:28
-	1422	(hydrogen near2 ion$1) near5 implant$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:29
-	47	((((xe adj arc) near2 lamp) or xenon) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))) and ((hydrogen near2 ion$1) near5 implant$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:29
-	19527	((xe adj arc) near2 lamp) or xenon near3 lamp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:30
-	330	(((xe adj arc) near2 lamp) or xenon near3 lamp) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:30
-	13	((((xe adj arc) near2 lamp) or xenon near3 lamp) and ((soi or (silicon near2 insulator) or soq or (silicon near2 quartz) or sof or (silicon near2 foreign)))) and ((hydrogen near2 ion$1) near5 implant$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 16:31
-	35	(flash near2 anneal$3) near5 (substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/21 20:53